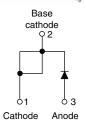


Vishay Semiconductors

HEXFRED® Ultrasoft Soft Recovery Diode, 16 A





TO-220AC

PRODUCT SUMMARY					
Package	TO-220AC				
I _{F(AV)}	16 A				
V_{R}	1200 V				
V _F at I _F	3.0 V				
t _{rr} (typ.)	30 ns				
T _J max.	150 °C				
Diode variation	Single die				

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified for industrial level





BENEFITS

- · Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- · Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA16TB120PbF is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 16 A continuous current, the VS-HFA16TB120PbF is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA16TB120PbF is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	V_{R}		1200	V		
Maximum continuous forward current	I _F	T _C = 100 °C	16			
Single pulse forward current	I _{FSM}		190	Α		
Maximum repetitive forward current	I _{FRM}		64			
Maximum nauga discination	Б	T _C = 25 °C	151	W		
Maximum power dissipation	P_{D}	T _C = 100 °C	60	VV		
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	°C		

VS-HFA16TB120PbF

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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V _{BR}	Ι _R = 100 μΑ		1200	-	-	
		I _F = 16 A		-	2.5	3.0	V
Maximum forward voltage	V_{FM}	I _F = 32 A	See fig. 1	-	3.2	3.93	
		I _F = 16 A, T _J = 125 °C	-	2.3	2.7		
Maximum reverse		V _R = V _R rated	Coo fig. 0	-	0.75	20	
leakage current	I _{RM}	$T_J = 125$ °C, $V_R = 0.8 \times V_R$ rated	See fig. 2	-	375	2000	μA
Junction capacitance	C _T	V _R = 200 V See fig. 3		-	27	40	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body		-	8.0	-	nH

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200$	I _F = 1.0 A, dI _F /dt = 200 A/μs, V _R = 30 V		30	-		
Reverse recovery time See fig. 5 and 10	t _{rr1}	T _J = 25 °C		-	90	135	ns	
See lig. 5 and 10	t _{rr2}	T _J = 125 °C		-	164	245		
Peak recovery current	I _{RRM1}	T _J = 25 °C	$I_F = 16 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	5.8	10	- A	
See fig. 6	I _{RRM2}	T _J = 125 °C		-	8.3	15		
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	260	675		
See fig. 7	Q _{rr2}	T _J = 125 °C		-	680	1838	nC	
Peak rate of fall of recovery current during t _b See fig. 8	dI _{(rec)M} /dt1	T _J = 25 °C		-	120	-	- A/µs	
	dI _{(rec)M} /dt2	T _J = 125 °C		-	76	-	Ανμδ	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C	
Thermal resistance, junction to case	R _{thJC}		-	-	0.83		
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	K/W	
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.50	-		
Weight			-	2.0	-	g	
vveigni			-	0.07	-	OZ.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style TO-220AC	HFA16TB120				

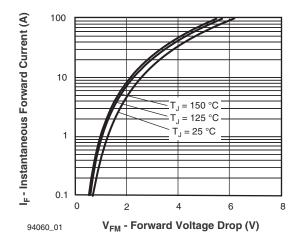




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= 150 °C I_R - Reverse Current (µA) 100 10 0.1 0.01 0 200 400 1000 600 800 1200 94060 02 V_R - Reverse Voltage (V)

Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward

Fig. 2 - Typical Reverse Current vs. Reverse Voltage

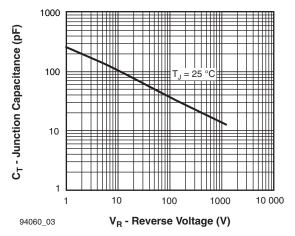


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

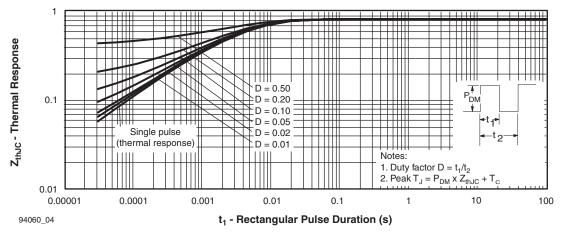


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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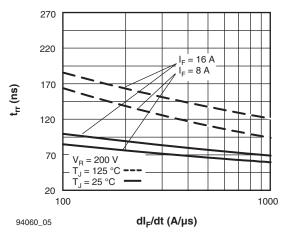


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt (Per Leg)

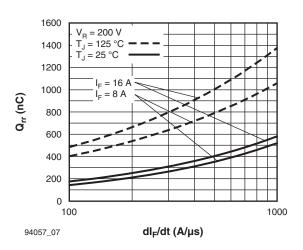


Fig. 7 - Typical Stored Charge vs. dl_F/dt (Per Leg)

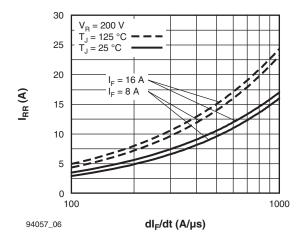


Fig. 6 - Typical Recovery Current vs. di_F/dt (Per Leg)

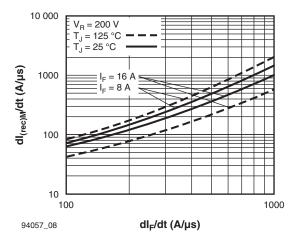


Fig. 8 - Typical dI_{(rec)M}/dt vs. dI_F/dt (Per Leg)



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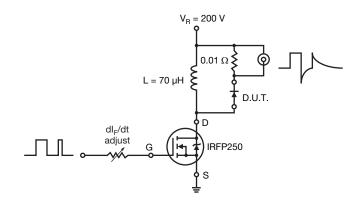
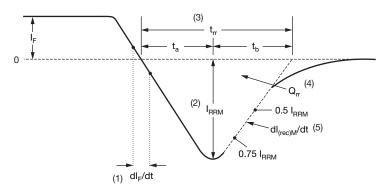


Fig. 9 - Reverse Recovery Parameter Test Circuit



- dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) Q_{rr} area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dl_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

VS-HFA16TB120PbF

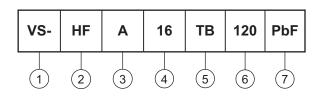
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HEXFRED® Ultrasoft Soft Recovery Diode, 16 A



ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product

HEXFRED® family

Electron irradiated

Current rating (16 = 16 A)

Package:

TB = TO-220AC

Voltage rating (120 = 1200 V)

PbF = Lead (Pb)-free

Tube standard pack quantity: 50 pieces

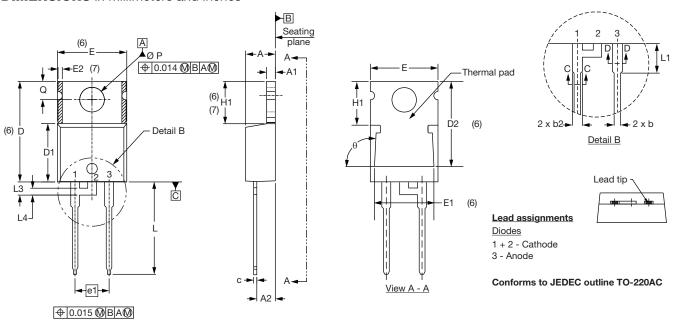
LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95221</u>					
Part marking information	www.vishay.com/doc?95224				



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TO-220AC

DIMENSIONS in millimeters and inches



SAMBOI	SYMBOL MILLIMETERS INCHES		NOTES		
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6
Е	10.11	10.51	0.398	0.414	3, 6

SYMBOL	MILLIN	IETERS	INCHES		NOTES	
STIMBUL	MIN.	MAX.	MIN.	MAX.	NOTES	
E1	6.86	8.89	0.270	0.350	6	
E2	-	0.76	-	0.030	7	
е	2.41	2.67	0.095	0.105		
e1	4.88	5.28	0.192	0.208		
H1	6.09	6.48	0.240	0.255	6, 7	
L	13.52	14.02	0.532	0.552		
L1	3.32	3.82	0.131	0.150	2	
L3	1.78	2.13	0.070	0.084		
L4	0.76	1.27	0.030	0.050	2	
ØΡ	3.54	3.73	0.139	0.147		
Q	2.60	3.00	0.102	0.118		
θ	90° t	o 93°	90° to 93°			

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimension: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline

Legal Disclaimer Notice



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